

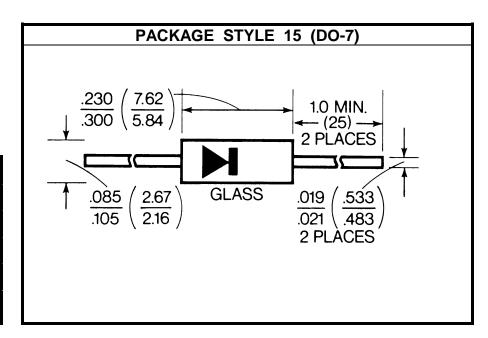
SILICON ABRUPT JUNCTION TUNING VARACTOR

DESCRIPTION:

The **AT6021** is an Epitaxial Silicon Abrupt Junction Microwave Tuning Varactor. This Device is Passivated With Silicon Dioxide Which Results in Very Low Leakage Current. The Capacitance Voltage Relationship Closely Approximates Square Law (n = 0.5).

MAXIMUM RATINGS

Ic	100 mA				
V_{CE}	70 V				
P _{DISS}	250 mW @ $T_C = 25$ °C				
TJ	-65 to +150 °C				
T _{STG}	-65 to +150 °C				
θ _{JC}	Jc 500 °C/W				



CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
V_{B}	$I_R = 10 \mu A$		70			V
C _T	V _R = 4.0 V	f = 1.0 MHz	44.65	47.0	49.35	pF
ΔC_{T}	C _{T0} /C _{T60}	f = 1.0 MHz	7.4			
ΔC_{T}	C _{T8} /C _{T60}	f = 1.0 MHz	2.50		2.60	
Q	V _R = 4.0 V	f = 50 MHz	600			